

REMARKS

Claims 1-27 are pending in this application, with claims 1, 5, 9, 13, 18, and 23 being independent. Claims 1, 5, 9 and 13 have been amended. In particular, claims 1 and 5 have been amended to each recite "wherein said first and third electrodes are each formed in different pixels." Claim 9 has been amended to recite "wherein a storage capacitor is constructed by said first electrode, said gate insulating film, and said second semiconductor film." Claim 13 has been amended to recite "wherein said gate wiring and said second electrode are provided on said same insulating film." Support for these amendments may be found in the application, for example, at pages 2 and 3 and Figs. 2A, 2B, 16 and 17.

Applicants acknowledge with appreciation the Examiner's allowance of claims 18-27 and the Examiner's indication that claims 2, 3, 6, 7, 10, 11, 15 and 16 are directed to allowable subject matter.

Independent claims 1, 5, 9 and 13, along with dependent claim 14, have been rejected as being anticipated by Segawa (U.S. Publication No. 2004/0150762). Claims 4, 8, 12 and 17, which depend from claims 1, 5, 9 and 13, respectively, have been rejected as being unpatentable over Segawa. Applicants have amended claims 1, 5, 9 and 13 to obviate these rejections.

Claims 1 and 5, as amended, each recite, among other elements, "said first and third electrodes are each formed in *different* pixels" (emphasis added). Applicants request reconsideration and withdrawal of the rejection of claims 1 and 5, and their dependent claims, because Segawa does not describe or suggest the recited first and third electrodes that are each formed in different pixels.

In Segawa, the two second gate electrodes 70, which the Examiner equates to the recited first and third electrodes, are not formed in different pixels. Rather, both of the second gate electrodes 70 are formed on the same pixel. See Fig. 1.

For at least this reason, applicants request reconsideration and withdrawal of the rejection of claims 1 and 5, and their dependent claims 4 and 8.

Claim 9, as amended, recites, among other elements, that "a *storage capacitor* is constructed by said first electrode, said gate insulating film, and said second semiconductor film"

(emphasis added). Applicants request reconsideration and withdrawal of the rejection of claim 9, and its dependent claims, because Segawa does not describe or suggest the recited storage capacitor.

In Segawa, one of the second gate electrodes 70, which the Examiner equates to the recited first electrode; the gate insulating film 12, which the Examiner equates to the recited gate insulating film; and the drain 13d, which the Examiner equates to the recited second semiconductor film, are all parts of a TFT of a display pixel, rather than parts that form a storage capacitor. Moreover, as shown in Fig. 2 of Segawa, the second gate electrode 70, the gate insulating film 12, and the drain 13d do not form a storage capacitor because the gate insulating film 12 is not positioned between the second gate electrode 70 and the drain 13d. Rather, the gate insulating film 12 is positioned between the drain 13d and the insulative substrate 10.

For at least these reasons, applicants request reconsideration and withdrawal of the rejection of claim 9 and its dependent claim 12.

Claim 13 recites a semiconductor device that includes a first electrode and an insulating film *formed on* the first electrode. A contact hole is provided in the insulating film and has a depth so as to reach the first electrode. A gate wiring is formed on the insulating film and connected with the first electrode through the contact hole. A second electrode is provided on the insulating film. Seventy percent of the area of the first electrode is overlapped with the second electrode. Claim 13 has been amended for clarity to recite "said gate wiring and said second electrode are provided on said *same* insulating film" (emphasis added). Applicants request reconsideration and withdrawal of the rejection of claim 13, and its dependent claims, because Segawa does not describe or suggest the recited first electrode on which is formed an insulating film and the recited gate wiring and second electrode provided on that same insulating film.

The Examiner asserts that Segawa discloses "a first electrode 70" and "an insulating film 15/12 formed on said first electrode." See page 4 of Office Action. Contrary to the Examiner's assertion, the gate insulating film 12 and interlayer insulating film 15, which the Examiner equates to the recited insulating film, are not formed on one of the second gate electrodes 70,

which the Examiner equates to the recited first electrode. Rather, as shown in Fig. 3 of Segawa, the second gate electrodes 70 are formed on the gate insulating film 12/interlayer insulating film 15, not vice versa.

Moreover, in Segawa, the gate signal line 51, which the Examiner equates to the recited gate wiring, is not provided on the same insulating film as the alignment film 20, which the Examiner equates to the recited second electrode. Applicants note that the Examiner may have meant to equate the reflective display electrode 19 with the recited second electrode rather than equating the alignment film 20 with the recited second electrode. The reflective display electrode 19, however, is also not provided on the same insulating film as the recited gate wiring. Rather, as shown in Fig. 2 of Segawa, the alignment film 20 and the reflective display electrode 19 are both provided on a planarizing insulating film 17, while the gate wiring 51 (including the part that serves as gate electrode 11) is provided on the insulative substrate 10.

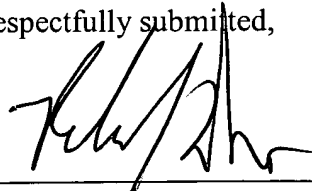
For at least these reasons, applicants request reconsideration and withdrawal of the rejection of claim 13 and its dependent claims 14 and 17.

Applicants submit that all claims are in condition for allowance.

Please apply any charges or credits to deposit account 06-1050.

Date: 11/22/05

Respectfully submitted,



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